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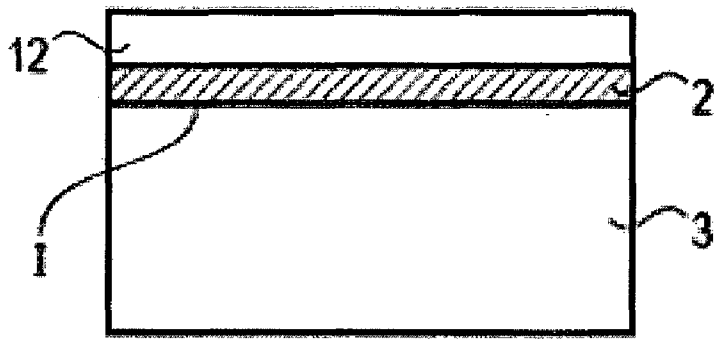
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(54) Title: METHOD OF TESTING A SEMICONDUCTOR ON INSULATOR STRUCTURE AND APPLICATION OF SAID TEST TO THE FABRICATION OF SUCH A STRUCTURE

FIG. 1D



(57) Abstract: The invention concerns a method of testing a semiconductor on insulator type structure comprising a support substrate (3), a dielectric layer (2) having a thickness of less than 50 nm and a semiconductor layer (12), said structure comprising a bonding interface (I) between the dielectric layer (2) and the support substrate (1) or the semiconductor layer (12) or inside the dielectric layer (2), characterized in that it comprises measuring the charge to breakdown (QBD) of said dielectric layer (2) and in that information is deduced from said measurement relating to the hydrogen concentration in said layer (2) and/or at the bonding interface (I). The invention also concerns a method of fabricating a batch of semiconductor on insulator type structures including carrying out said test on a sample structure from said batch.

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